1. **(Once Amended)** A semiconductor laser device, comprising:

a doped semiconductor cladding layer;

an undoped semiconductor optical confinement layer;

an undoped semiconductor spacer layer positioned between said cladding layer and said optical confinement layer and in contact with both said cladding layer and said optical confinement layer;

a light-generating layer disposed over said optical confinement layer; and

a first electrode and second electrode for supplying an electrical current to said light generating layer.

2. **(Once Amended)** The laser device of claim 1, wherein said undoped spacer layer has a thickness which is less that the thickness of said cladding layer and which is more than about 4 nm.

12. **(Once Amended)** A semiconductor laser device, comprising:

a semiconductor substrate;

an n-doped semiconductor lower cladding layer;

an undoped semiconductor lower optical confinement layer;

an undoped semiconductor spacer layer between said lower cladding layer and said lower optical confinement layer and in contact with both said cladding layer and said optical confinement layer;

a semiconductor active layer for generating light;

a semiconductor upper optical confinement layer;

a p-doped semiconductor upper cladding layer; and

electrodes for current injection to said device.

13. **(Once Amended)** The laser device of claim 12, wherein said undoped spacer layer has a thickness which is less that the thickness of said cladding layer and which is more than about 4 nm.

20. **(Once Amended)** A method of making a semiconductor laser device, comprising the steps of:

forming an n-doped semiconductor lower cladding layer on a substrate;

forming an undoped semiconductor spacer layer over said lower cladding layer and in contact therewith;

forming an undoped semiconductor optical confinement layer over said spacer layer and in contact therewith;

forming an active, light emitting semiconductor layer over said optical confinement layer, and

forming a first electrode and a second electrode for supplying an electrical current to said active, light emitting semiconductor layer.

28. **(Once Amended)** The laser device of claim 20, wherein said undoped spacer layer has a thickness which is less that the thickness of said cladding layer and which is more than about 4 nm.

29. **(Once Amended)** A semiconductor device comprising:

a first III – V semiconductor layer formed by MOCVD of n-doped semiconductor material,

a III – V semiconductor spacer layer formed by MOCVD of undoped semiconductor material deposited directly on said first III – V semiconductor layer,

a second III – V semiconductor layer formed by deposition of undoped semiconductor material directly on said spacer layer, whereby lattice defects caused by said first III – V semiconductor layer are mitigated by said spacer layer, and

a first electrode and second electrode for sending an electrical current through said III-V semiconductor layers.

30. **(Once Amended)** A method of making a III – V semiconductor device, comprising the steps of:

depositing a layer of a III – V semiconductor compound doped with selenium using MOCVD;

depositing a spacer layer of an undoped III – V semiconductor compound directly on said selenium-doped layer using MOCVD;

depositing an undoped layer comprising one or more III – V semiconductor compounds directly on said spacer layer, and

forming a first electrode and second electrode for sending an electrical current through said layers.

Please add New Claims 31-43:

31. **(New)** The method of Claim 30 wherein the first layer and the spacer layer are deposited by a single MOCVD process which is interrupted for a period of time after the layer of selenium-doped III – V semiconductor compound is deposited and before the spacer layer is deposited.

32. **(New)** The semiconductor laser device of Claim 1 wherein said optical confinement layer comprises a quaternary compound material.

33. **(New)** The method of Claim 20 wherein said optical confinement layer comprises a quaternary compound material.

34. **(New)** The semiconductor device of Claim 29 wherein said optical confinement layer comprises a quaternary compound material.

35. **(New)** The semiconductor device of Claim 30 wherein said optical confinement layer comprises a quaternary compound material.

36. **(New)** A semiconductor laser device, comprising:

a doped semiconductor cladding layer;

a semiconductor optical confinement layer; and

an undoped semiconductor spacer layer positioned between the cladding layer and the optical confinement layer, the spacer layer comprising a strain compensated superlattice layer.

37. **(New)** A semiconductor laser device, comprising:

a doped semiconductor cladding layer;

a semiconductor optical confinement layer comprising a quaternary compound;

an undoped semiconductor spacer layer positioned between said cladding layer and said optical confinement layer;

a light-generating layer disposed over said optical confinement layer; and

a first electrode and second electrode for supplying an electrical current to said light generating layer.

38. **(New)** The laser device of claim 37, wherein said undoped spacer layer has a thickness which is less that the thickness of said cladding layer and which is more than about 4 nm.

39. **(New)** The laser device of claim 37 wherein the n-doping material in said cladding layer is selenium.

40. **(New)** The laser device of claim 37 wherein said undoped spacer layer consists of a single layer of quaternary material having a bandgap-wavelength in the range of 0.92 μm – 1.1 μm.

41. **(New)** The laser device of claim 37 wherein said undoped spacer layer consists of a graded composition layer of quaternary material having a bandgap in the range of 0.92 μm – 1.1 μm.